1. General description

NPN/PNP Resistor-Equipped double Transistors (RET) in a leadless ultra small DFN1412-6 (SOT1268) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- Low package height of 0.5 mm
- AEC-Q101 qualified

3. Applications

- Digital applications
- Cost-saving alternative to BC847/BC857 series in digital applications
- · Control of IC inputs
- Switching loads

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor,	Per transistor, for the PNP transistor with negative polarity							
V _{CEO}	collector-emitter voltage	open base		-	-	50	V	
Io	output current			-	-	100	mA	
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 5 mA; T_{amb} = 25 °C		60	-	-		
R1	bias resistor 1		[1]	15.4	22	28.6	kΩ	
R2/R1	bias resistor ratio		[1]	8.0	1	1.2		

[1] See section "Test information" for resistor calculation and test conditions.



50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix}$	
3	O2	output (collector) TR2	2 5	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	3 8 4	TR1 R2 R1
6	O1	output (collector) TR1		<u> </u>
7	O1	output (collector) TR1	Transparent top view	
8	O2	output (collector) TR2	DFN1412-6 (SOT1268)	GND1 I1 O2 aaa-007379

6. Ordering information

Table 3. Ordering information

Type number	Package	e					
	Name	Description	Version				
PRMD2		plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 mm x 1.2 mm x 0.47 mm	SOT1268				

7. Marking

Table 4. Marking codes

Type number	Marking code
PRMD2	B4

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

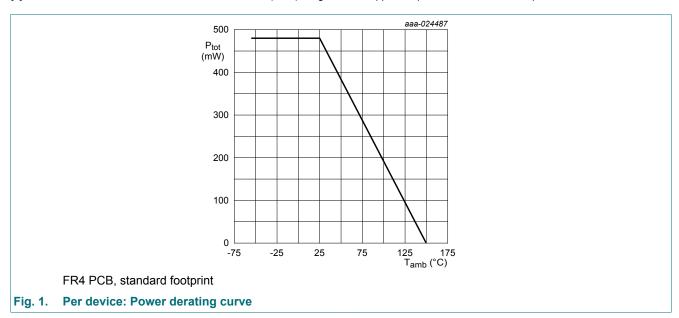
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or, for the PNP transistor wit	n negative polarity				
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	10	V
V _I	input voltage			-10	40	V
Io	output current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
Per device				1		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	480	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	er transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	261	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

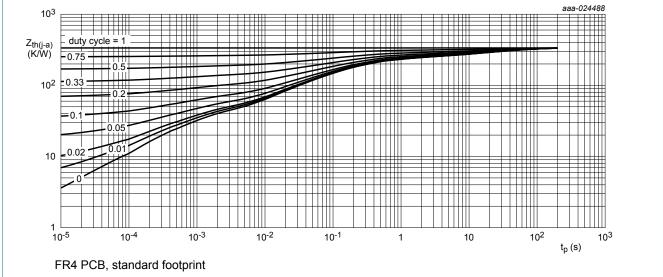


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or, for the PNP transistor v	vith negative polarity					
I _{CEO}		V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	1	μΑ
	current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C		-	-	5	μΑ
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	180	μΑ
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 5 mA; T _{amb} = 25 °C		60	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	150	mV
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C		-	1.1	0.8	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		2.5	1.7	-	V
R1	bias resistor 1		[1]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[1]	0.8	1	1.2	
C _C	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	2.5	pF
		V_{CB} = -10 V; I_{E} = 0 mA; I_{e} = 0 mA; I_{e} = 1 MHz; I_{amb} = 25 °C		-	-	3	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	230	-	MHz
		V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C		-	180	-	MHz

- [1] See section "Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor

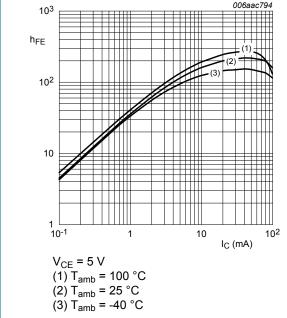


Fig. 3. NPN transistor: DC current gain as a function of collector current; typical values

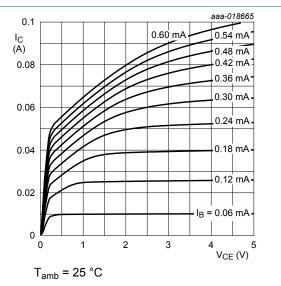
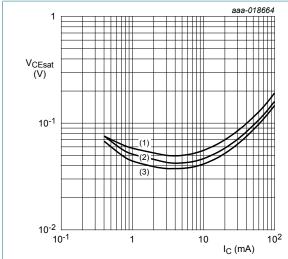


Fig. 4. NPN transistor: Collector current as a function of collector-emitter voltage; typical values

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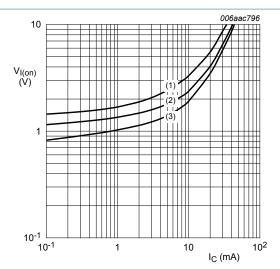


$$I_{\rm C}/I_{\rm B} = 20$$

$$(1) T_{amb} = 100 ° ($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 5. **NPN** transistor: Collector-emitter saturation voltage as a function of collector current; typical values

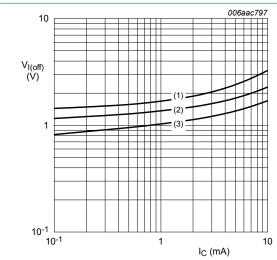


$$V_{CE} = 0.3 V$$

$$(1) T_{amb} = -40 ° ($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 6. NPN transistor: On-state input voltage as a function of collector current; typical values



$$V_{CE}$$
 = 5 V

$$(1) T_{amb} = -40 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. NPN transistor: Off-state input voltage as a function of collector current; typical values

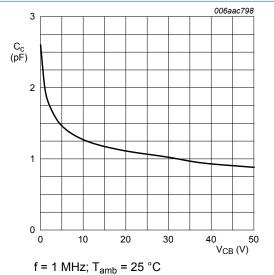
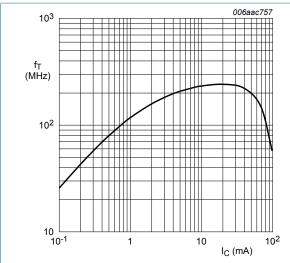


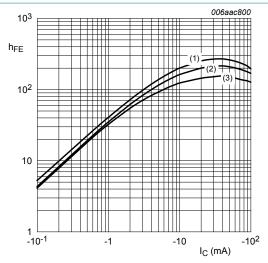
Fig. 8. NPN transistor: Collector capacitance as a function of collector-base voltage; typical

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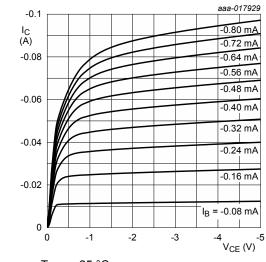
 V_{CE} = 5 V; T_{amb} = 25 °C

Fig. 9. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



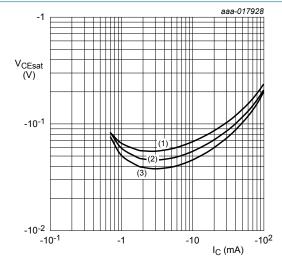
V_{CE} = -5 V (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 20$

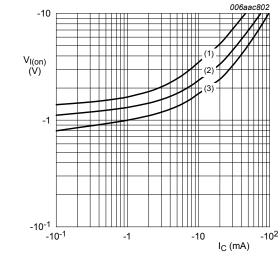
(1) T_{amb} = 100 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 12. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)



$$V_{CE}$$
 = -0.3 V

$$(1) T_{amb} = -40 ° ($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 13. PNP transistor: On-state input voltage as a function of collector current; typical values

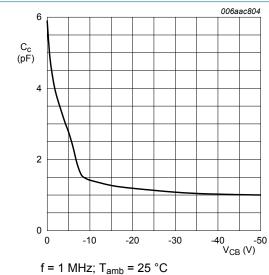
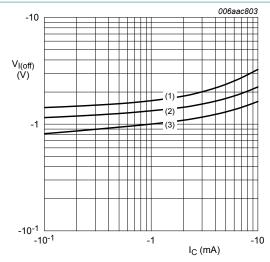


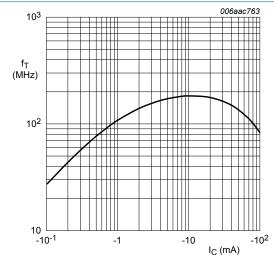
Fig. 15. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values



$$(1) T_{amb} = -40 ° ($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 14. PNP transistor: Off-state input voltage as a function of collector current; typical values



 V_{CE} = -5 V; T_{amb} = 25 °C

Fig. 16. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

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11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

Resistor calculation

Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

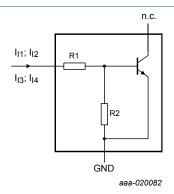


Fig. 17. NPN transistor: Resistor test circuit

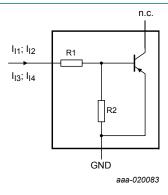


Fig. 18. PNP transistor: Resistor test circuit

Resistor test conditions

Table 8. Resistor test conditions

Per transistor; for the PNP transistor with negative polarity

R1 (kΩ)	R2 (kΩ)	Test conditions	est conditions					
		I _{I1}	I ₁₂	I ₁₃	I ₁₄			
22	22	150 μΑ	230 μΑ	-150 μA	-230 µA			

PRMD2

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12. Package outline

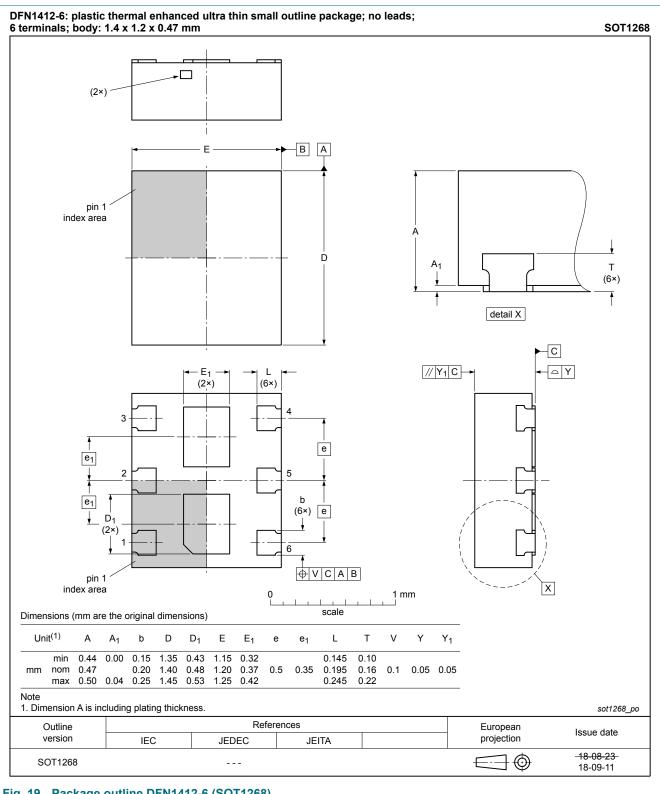
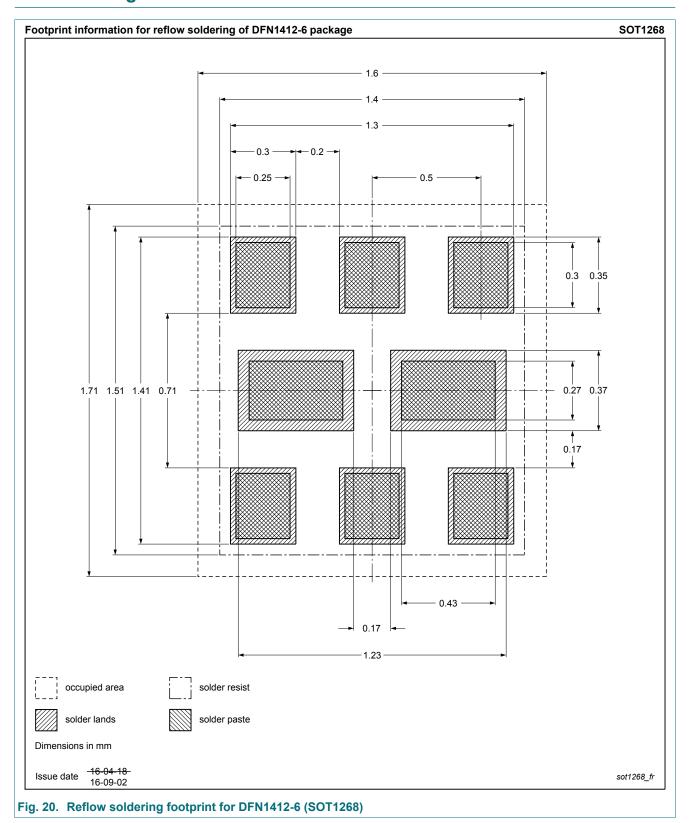


Fig. 19. Package outline DFN1412-6 (SOT1268)

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13. Soldering



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14. Revision history

Table 9. Revision history

,							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PRMD2 v.2	20180914	Product data sheet	-	PRMD2 v.1			
Modifications:	Package outline draw	Package outline drawing updated: Unit T added					
PRMD2 v.1	20170614	Product data sheet	-	-			

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50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PRMD

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